

Electronic structure of Diluted Magnetic Semiconductors $Ga_{1-x}Mn_xN$ and $Ga_{1-x}Cr_xN$

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Abstract. We have undertaken a study of diluted magnetic semiconductors $Ga_{1-x}Mn_xN$ and $Ga_{1-x}Cr_xN$ with $x = 0.0625, 0.125$, using the all electron linearized augmented plane wave method (LAPW) for different configurations of Mn as well as Cr. We study four possible configurations of the impurity in the wurtzite GaN structure to predict energetically most favorable structure within the 32 atom supercell and conclude that the near-neighbor configuration has the lowest energy. We have also analyzed the ferro-magnetic as well as anti-ferromagnetic configurations of the impurity atoms. The density of states as well as bandstructure indicate half metallic state for all the systems. T_c has also been estimated for the above systems.

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1. Introduction

Gallium nitride is one of the most promising materials among the diluted magnetic semiconductor (DMS) material for application in spintronics. By doping transition metal (TM) atoms, Mn or Cr, local magnetic moment are introduced in semiconductor which mediate ferromagnetically. (Ga,Cr)N based DMS was predicted to show high T_c [1] for high enough concentration of Cr and further Hashimoto *et al.* [2] observed that (Ga,Cr)N based DMS grown by ECR molecular beam epitaxy showed T_c above 400K. Cr⁺-implanted GaN, studied by photoluminescence and superconducting quantum interference device (SQUID) reveal that the implanted Cr⁺ incorporates substitutionally at Ga site and the ferromagnetic order is retained upto 300K [3]. Takeuch *et al.* [4]. have reported a systematic study of changes in the occupied and unoccupied N-partial density of states (DOS) and confirm the wurtzite N 2- p DOS and substitutional doping of Cr into Ga sites using SXES and XAS. Recently, ferromagnetism above 900K was reported in Cr-GaN thin films [5]. Theoretically it was predicted that the ferromagnetic (FM) interaction in (Ga,Mn)N may be retained upto room temperature [6]. The initial reports of high T_c in (Ga,Mn)N were followed by controversial results where the reported T_c varied between 20K - 940K [7, 8, 9, 10]. Zajac and coworkers observed Mn ions in Ga_{1-x}Mn_xN ($x < 0.1$) crystals coupled anti-ferromagnetically (AFM) [11]. Electronic structure and magnetic properties of zinc blende Ga_{1-x}Mn_xN for several values of x with varied spatial distribution of dopant atoms to understand the magnetic interaction for explanation of FM-AFM competition is discussed by Uspenskii *et al.* [12] where the calculations were done using the tight binding LMTO method in the local spin density approximation. Sanyal and Mirbt [13] have studied Mn doped GaAs and GaN DMS using the *ab-initio* plane wave code (VASP) within density functional theory (DFT). They have determined the interatomic exchange interactions by substituting Mn in various positions in the unit cell and have attributed the origin of ferromagnetism in (Ga,Mn)N to double-exchange mechanism involving the hopping of Mn- d electrons. Raebiger *et al.* [14] used the full potential linearized augmented plane wave (FP-LAPW) method to investigate the interplay between clustering and exchange coupling in magnetic semiconductor Ga_{1-x}Mn_xAs. They have studied all possible arrangements of the two Mn atoms on Ga sublattice for $x \sim 6\%$ and found that clustering of Mn atoms at near neighbour Ga sites is energetically preferred. Our analysis of the wurtzite GaN doped with Mn or Cr is motivated by the latter study.

2. Method and Computational Details

We have employed the spin-polarized Linearized Augmented Plane Wave Method (FP-LAPW) as implemented in the WIEN2K package [15] with the Generalized Gradient Approximation (GGA) for the exchange-correlation potential proposed by Perdew, Burke and Ernzerof (PBE96) [16]. This is state-of-the-art electronic structure method, which does not use any shape approximation for the potential, to solve the Kohn-Sham

type of equations self-consistently.

GaN normally occurs in the wurtzite structure with lattice constants $a = 3.19\text{\AA}$ and $c = 5.19\text{\AA}$, giving c/a ratio of 1.62. Each Ga is tetrahedrally bonded to N atoms at an average distance of $1.95\text{\AA}$ and each N in turn is surrounded by four Ga neighbors. The calculations for DMS were performed within a 32 atom supercell, constructed from $2 \times 2 \times 2$ standard unit cell of wurtzite structure wherein the dopant is substituted at various cation sites, since it has been shown that the formation energy for interstitial Mn doping is higher than substitutional doping [13]. The supercell approach is used to restrict the dopant concentration to a small value, which is of interest for studying magnetic properties of the system, without altering the original underlying lattice structure. Our interest was in observing the changes in the electronic structure of the DMS with respect to the possible different geometries of the dopants within the host semiconductor. Self-consistent electronic structure calculations were performed using the APW + local orbitals (lo) basis set for the valence and semi-core electrons with $R_{MT} * K_{max} = 7$, $l_{max} = 10$ and total energy convergence of $0.00001 Ry$. The Muffin-Tin radii for Ga, Mn and Cr were kept at $2.0\text{\AA}$ and that for N at $1.6\text{\AA}$. Spin-polarized calculations were carried out to observe the effect of spin-splitting and to calculate the on-site magnetic moment at TM site.

We have studied wurtzite GaN doped with one TM atom impurity, which is $\sim 6.25\%$ doping and two identical TM atoms in the 32 atom unit cell amounting to $\sim 12.5\%$ doping. To simulate different surroundings for the transition metal (TM) atoms we have spanned certain geometries within the 32 atom unit cell wherein the distance between the dopants is varied. In the case of the single impurity substitution, the nearest distance between two TM atoms is $6.38\text{\AA}$ in plane and $10.38\text{\AA}$ along the c -axes. We have studied four different geometries of two TM atom substitutions at $3.19\text{\AA}$, near neighbor (nn), $4.5\text{\AA}$, $5.19\text{\AA}$ and $6.08\text{\AA}$ separations. When two near neighbor (nn) Ga atoms are substituted by TM atoms the in-plane TM-TM atoms distance is $3.19\text{\AA}$ and along the c -axes it is $10.38\text{\AA}$. For the second case the out-of-plane distance is $4.5\text{\AA}$ and the in-plane distance between the dopants is $6.3\text{\AA}$. In the third case, two Ga atoms lying one above the other, along the z -axes, separated by a distance of $5.19\text{\AA}$ are substituted by TM atoms and the in-plane TM atoms are at $6.38\text{\AA}$. The last case is such that the in-plane separation ($6.38\text{\AA}$) and out of plane separation ($6.09\text{\AA}$) between the TM atoms is comparable. For estimating the magnetically favorable system, the spins of the dopants are aligned along the same direction, corresponding to the FM configuration, and aligned in the opposite directions corresponding to AFM configuration. The self consistency was achieved on a mesh of $5 \times 5 \times 2$ k-points.

Structural relaxation for the TM site and the nn N sites was carried out to observe changes in the bond lengths between TM and the first shell of N atoms. Very small change ($\sim 3 - 4\%$) was observed in the bond lengths and no significant changes were seen in the band structure in agreement with the earlier reported results [17]. Thus the calculations reported here are for systems without allowing any relaxation.

3. Results

In the wurtzite GaN semiconductor, each Ga (N) is tetrahedrally bonded to 4 N (Ga) atoms. Pure GaN is a direct band gap semiconductor with top of the valence band consisting of N p -states and the bottom of the conduction band having Ga sp -character. The Ga d levels are deep and do not take part in the bonding. Thus they are treated as core states. The band gap of GaN, which is underestimated by density functional theory within the approximation used for the exchange correlation energy functional, is $\sim 2\text{eV}$. The experimentally determined band gap of undoped GaN is $\sim 3.4\text{eV}$. Das *et al.* [18] have shown that, for Mn atoms to couple ferromagnetically, they need to be kept apart by more than the critical distance of $2.5\text{\AA}$. Similar calculations on clusters of (GaN)Cr indicate that the critical Cr-Cr distance is $2.7\text{\AA}$ [19]. In all our calculations the distance between the dopants was greater than the corresponding critical distances.

3.1. Mn doped systems

Localized magnetic moments are introduced within the GaN system by substituting the cations with TM impurity atom(s). Mn atom with $4s^2$ and $3d^5$ electrons in the valence region replaces Ga atom with valency $4s^2 4p^1$. On substitution Mn atoms contributing five d levels per atom are thus expected to contribute to the observed magnetic moment. Since three of the valence electrons from Mn go into compensating the three electron

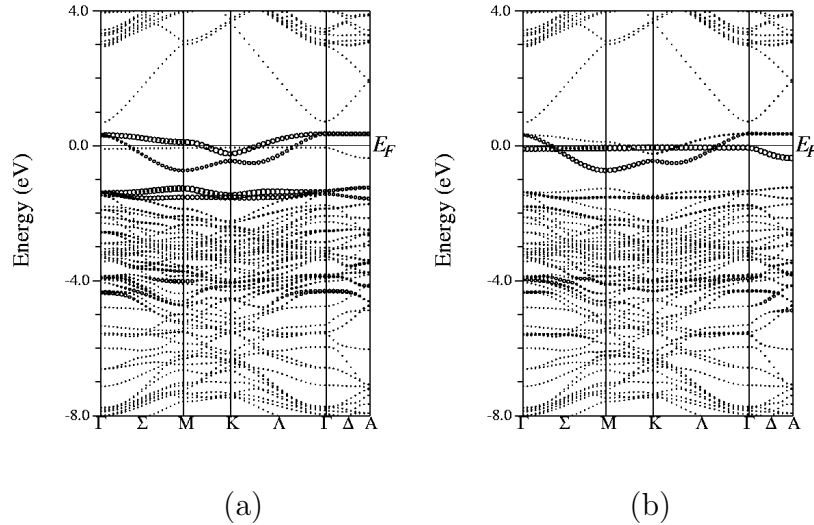


Figure 1. Mn-projected majority spin (a) d_{t_2} and (b) d_e bands in $Ga_{15}MnN_{16}$.

states of substituted Ga, one hole per Mn is introduced into the system. Figure 1 shows the Mn-projected d_{t_2} and d_e majority spin electronic structure for $Ga_{15}MnN_{16}$. The Mn- d states lie at the top of the valence band and cross the ϵ_F in some places. These are split into d_e and d_{t_2} states, the d_{t_2} level is two thirds filled and the d_e is almost occupied.

The minority spin levels are empty and lie above the ϵ_F indicating 100% spin-polarized states. The Mn induced states lie in the gap region of GaN. The top of the valence band in GaN is composed of the N- p levels and the unique properties, particularly the half metallic state of DMS, thus arise from the TM d and host p interactions that couple the two subsystems.

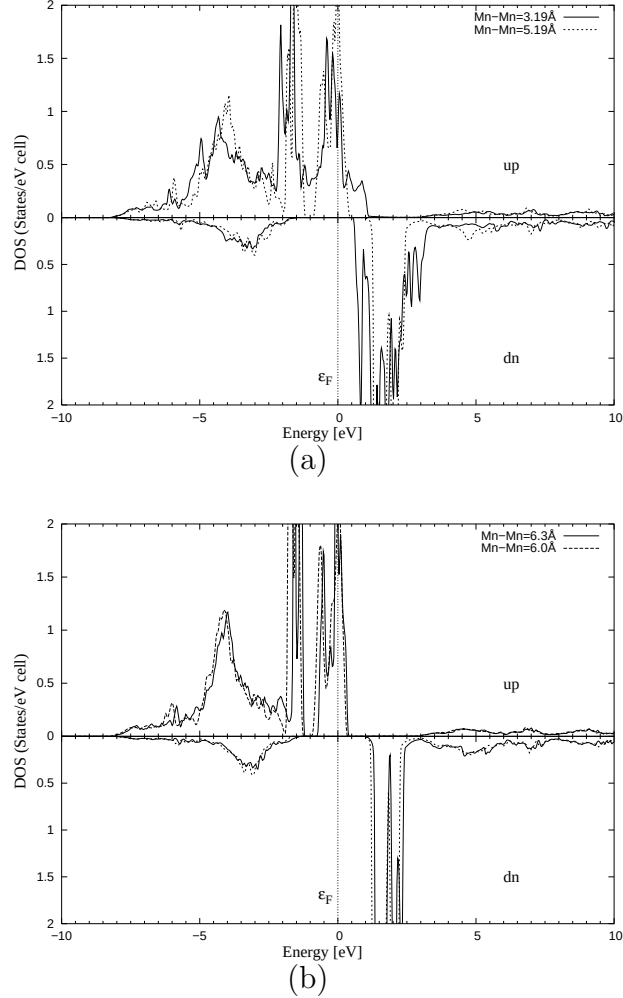


Figure 2. Mn-projected d -DOS in $Ga_{14}Mn_2N_{16}$ (a) with Mn-Mn distance equal to 3.19 Å and 5.19 Å and (b) 6.0 Å and 6.3 Å. The upper and lower panels represent the majority and minority spin DOS respectively.

In order to understand the variation of exchange interaction among the TM impurity with the distance between the TM atoms, the concentration of Mn atoms was increased to 12.5%, equivalent to introducing 2 Mn atoms in the supercell. Self consistent calculations were carried out for two different magnetic configurations of Mn electrons in which the electrons are parallel or antiparallel corresponding to FM or AFM configuration. For all the geometries of the dopants, systems, as described in section II, with FM configuration of the Mn atoms were found to have lower energy. Since the Mn- d levels are responsible for observed half metallic behavior, a comparison of Mn- d DOS in various geometries is shown in figure 2, (a) for separations 3.19 Å and 5.2 Å and

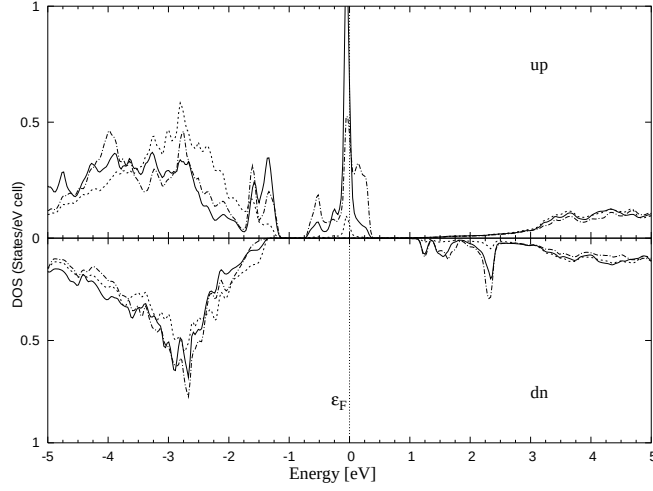
(b) for $6.0\text{\AA}$ and $6.3\text{\AA}$. Here the half metallic state is evident in all the cases. The TM-TM distance of $6.3\text{\AA}$ corresponds to single TM doping (6.25%).

The Mn d -DOS is broad for substitution at nn distance. In all the other cases the band is split indicating that the majority spin d -bands of the two Mn atoms at nn overlap. On increasing Mn-Mn distance, d -band splitting takes place implying a reduction in the interaction between the TM atoms. It may be noted that the minority spin conduction band overlaps with the majority spin band for nn substitution. A gap of $\sim 0.5\text{eV}$ is present between the minority spin conduction band and majority spin band for Mn-Mn distance greater than nn. The minority spin valence band as well as conduction band is far apart from the ϵ_F thus retaining the highly spin polarized state also seen in the single Mn doped $Ga_{14}MnN_{16}$ system. The down spin gap is 2eV for nn configuration and increases to 2.5eV at larger separations. On increasing the distance between the Mn atoms, splitting of d -level increases. This is consistent with the observation that in single impurity doping, TM-TM atom distance is $6.0\text{\AA}$ and splitting of the Mn- d band is larger as seen in figure 2(b). The magnetic moment at Mn-site does not depend on the distance between the dopant atoms and has a value $3.34\mu_B$ for all the geometries as indicated in table 1.

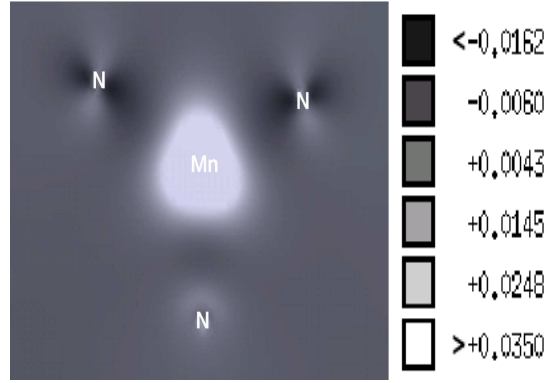
Table 1. Magnetic moment(μ_B) in various Mn-doped systems. Total_{mom} indicates mag. mom./unit cell, dopant_{mom} is the mag. mom. at dopant site and N_{mom} is the average mag. mom. at nn N sites.

System	Total _{mom}	Dopant _{mom}	N _{mom}
$Ga_{15}MnN_{16}$	4.00	3.33	0.001
$Ga_{14}Mn_2N_{16}$	8.00	3.34	0.001
Mn-Mn = $3.19\text{\AA}$			
$Ga_{14}Mn_2N_{16}$	8.00	3.34	0.005
Mn-Mn = $4.5\text{\AA}$			
$Ga_{14}Mn_2N_{16}$	8.00	3.33	0.006
Mn-Mn = $5.19\text{\AA}$			
$Ga_{14}Mn_2N_{16}$	8.00	3.34	0.005
Mn-Mn = $6.0\text{\AA}$			

The presence of localized moment influences the near neighbor N atoms within the GaN system, such that DOS of the nn N-atoms around the impurity atom becomes as shown in figure 3(a). Due to the $p-d$ interaction, induced states are seen on N atoms. The magnitude of the induced states is maximum at nn N atoms and decreases as the distance from the TM atom increases. This again indicates a localized nature of the TM states. Figure 3(b) shows the spin charge density (SCD) in a plane containing three nn N atoms for single Mn doping. The plot shows that the SCD on the N atoms lying above the Mn atom is negative whereas it is positive for the N atom lying below the Mn atom. Average magnetic moment on the nn N atoms is positive as shown in table 1 for all the different geometries.



(a)



(b)

Figure 3. (a) Variation in partial-DOS at 3 N-sites in $Ga_{15}MnN_{16}$. The solid lines: nn-N along c -axis. Dotted lines: nn-N in plane. Dashed-dotted lines: next nn-N (b) SCD plot in a plane of three nn N atoms.

3.2. Cr doped systems

Electronic structure calculation for substitutional doping of Cr in the GaN system was also done and is analyzed in a similar fashion. For each Cr doped in the 32 atom supercell, equivalent to 6.25% doping, there are five spin up d -states which are introduced in the GaN band gap. Since the Cr atom has $4s^23d^4$ valence electrons, only three of the electron states out of the five $3-d$ levels are occupied, thus creating two hole states per Cr substitution. Single Cr doping into the 32 atom supercell at cation site results in the Cr- d levels appearing in the band gap of the semiconductor host as seen in figure 4. The Cr d_{t_2} levels split (figure 4(a)), out of which two energy levels lie below the Fermi level (ϵ_F) and are occupied. The third level which is ~ 0.5 eV above is unoccupied. One of the d_e level is occupied and the other lies just above the ϵ_F as seen in figure 4(b). However, the hybridization of d_{t_2} and d_e majority spin states is negligible and these levels are well separated as opposed to Mn doped case. As in the case of Mn doping, the Cr minority spin d -states are above the ϵ_F and so the impurity states at the

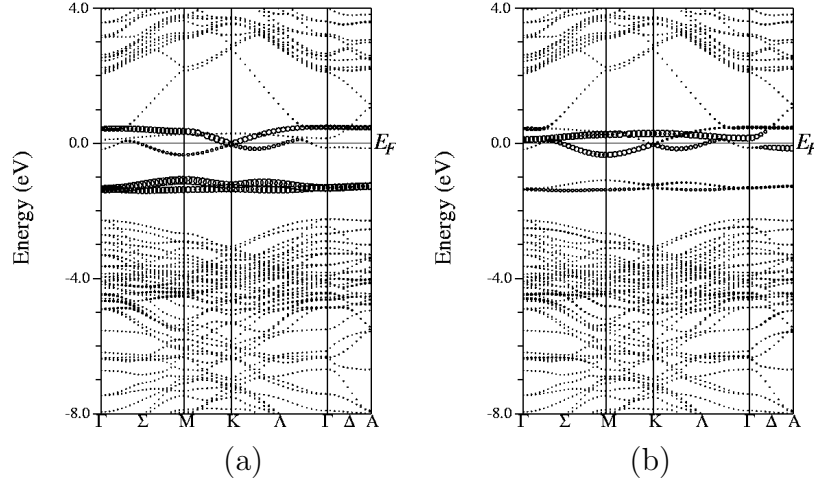


Figure 4. Cr-projected majority spin (a) d_{t_2} and (b) d_e bands in $Ga_{15}CrN_{16}$.

ϵ_F are 100% spin polarized.

In the $Ga_{14}Cr_2N_{16}$ system, figure 5 shows that even though the Cr atoms are substituted at nn sites there is a gap seen between the split Cr- d levels, unlike in the nn Mn-doped system. The minority spin conduction band overlaps with the majority spin band for nn Cr case, as in nn Mn case. For all the geometries of the dopant atoms the system is half metallic. The band gap for the minority spin, in case of two Cr substitution at 3.19Å is ~ 3 eV which is larger than the corresponding Mn case which has a gap of ~ 2.0 eV. When the TM-TM distance is 5.19Å, in the Cr case the gap is ~ 3.0 eV whereas for Mn substitution it is ~ 2.5 eV. The lowest energy configuration for Cr substitution occurs for Cr-Cr distance of 3.19Å and for all the geometries studied the FM configuration of TM atoms has lower energy compared to AFM configuration. The magnetic moments at the Cr site in various geometries is as shown in table 2 and it is seen that the magnetic moment does not show much variation depending on the distance, indicating that the direct interaction between the Cr atoms is minimal.

Table 2. Magnetic moment(μ_B) in Cr-doped systems. Total_{mom} indicates mag. mom./unit cell, dopant_{mom} is the mag. mom. at dopant site and N_{mom} is the average mag. mom. at nn N sites.

System	Total _{mom}	Dopant _{mom}	N _{mom}
$Ga_{15}CrN_{16}$	3.00	2.47	-0.025
$Ga_{15}Cr_2N_{16}$ Cr-Cr = 3.19 Å	6.00	2.48	-0.031
$Ga_{15}Cr_2N_{16}$ Cr-Cr = 4.5 Å	6.00	2.47	-0.022
$Ga_{15}Cr_2N_{16}$ Cr-Cr = 5.19 Å	6.00	2.48	-0.025
$Ga_{15}Cr_2N_{16}$ Cr-Cr = 6.0 Å	6.00	2.48	-0.026

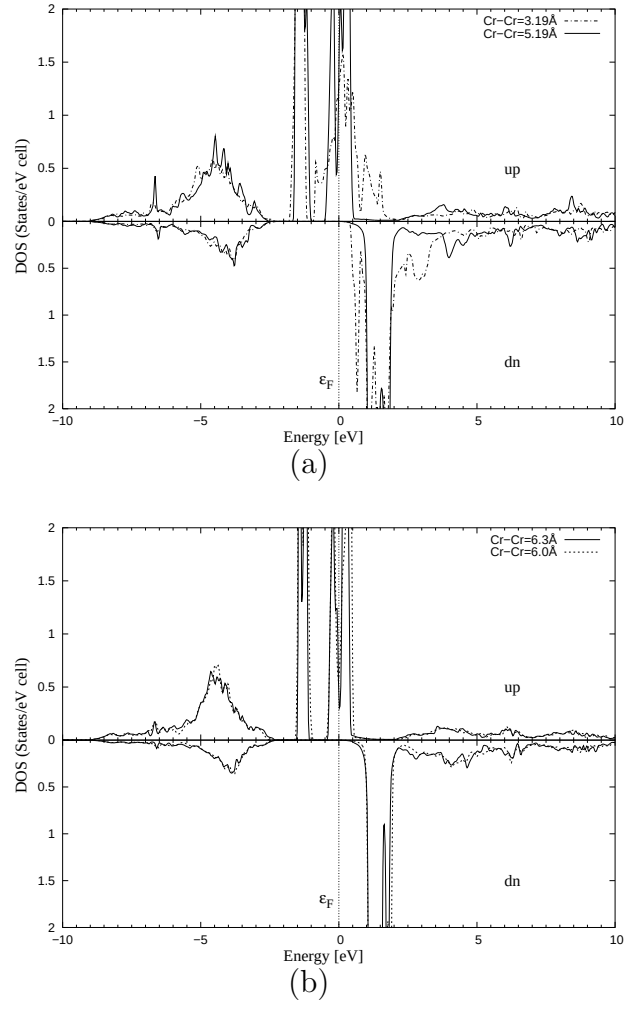


Figure 5. Cr-projected d -DOS in $Ga_{14}Cr_2N_{16}$ for Cr-Cr separation of (a) 3.19 Å and 5.19 Å and (b) 6.0 Å and 6.3 Å.

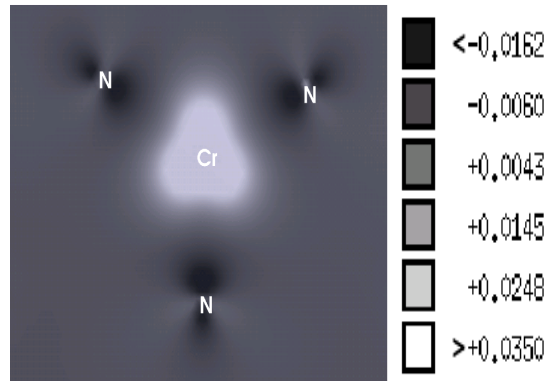


Figure 6. SCD plot in a plane of three nn N atoms around the TM atom in $Ga_{14}CrN_{16}$.

Magnetic moments observed at the various dopant sites from our calculation are shown in the table 2. The total magnetic moment per unit cell per Mn atom is $4\mu_B$ and

the average magnetic moment on the nn N atoms in case of Mn-doping is parallel to the Mn-moment. This can be understood as penetration of the spin-polarized Mn states to the neighboring host which does not have any of its own states in the gap region. The magnetic moment per unit cell per Cr atom is $3\mu_B$. The average magnetic moment on the nn N atom is anti-parallel to Cr-moment. The difference in the orientation of the average magnetic moment on nn N atoms of Mn and Cr is due to the difference in the p DOS of the nn N along the z axis (figure not shown here) compared to the nn N atoms lying in the xy plane above the TM atoms. There is not much variation of magnetic moment with increase in Cr-Cr distance and shows a similar trend as Mn doped systems. The magnitude of average nn-N magnetic moment is greater in case of Cr substitution, which contribute one less electron to the hybridized valence band. SCD in figure 6 on all of the nn-N atoms of the single Cr (only 3 nn N atoms shown in figure 6) doped system is negative thus showing that the TM atom and the nn-N are anti-ferromagnetically coupled.

3.3. Estimation of T_c

We have predicted the T_c for the DMS based on $\text{Ga}_{16}\text{Mn}_2\text{N}_{16}$ and $\text{Ga}_{16}\text{Cr}_2\text{N}_{16}$ considering the mean field approximation. Figure 7 shows the $\Delta E = E_{AFM} - E_{FM}$ for the Mn/Cr

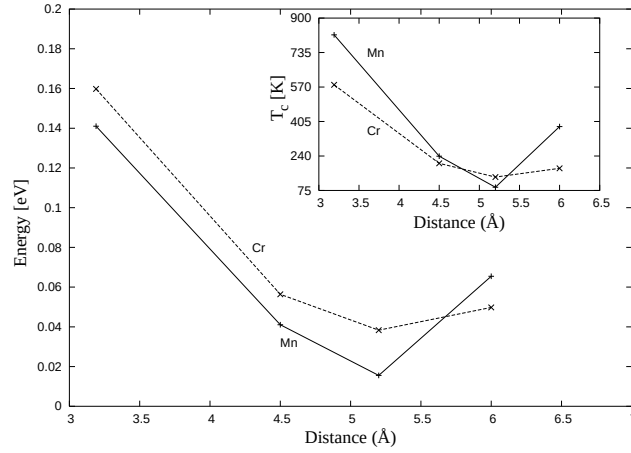


Figure 7. $\Delta E = E_{AFM} - E_{FM}$ for Mn and Cr doping. Inset shows the mean field T_c variation with distance between dopants.

doped systems, where E_{AFM} is the total energy for the antiferromagnetic (AFM) configuration and E_{FM} is the total energy for the ferromagnetic (FM) configuration. Observed variation ΔE vs distance for Mn substituted DMS agrees with the one reported by Sanyal [13]. ΔE is a measure of the exchange interaction in the system. Highest ΔE is seen for the case where the TM atoms are substituted as near neighbors, signifying larger overlap of the magnetic impurity orbitals. For Mn doping at nn $\Delta E \sim 0.14\text{eV}$, this compares well with the value calculated for dimer substitution by Uspenskii *et. al* [12] which compared qualitatively with the high $T_c = 940\text{K}$ measured [9]. As for the identical Cr case $\Delta E \sim 0.16\text{eV}$ also compares well with the observed T_c but is

lower than the 900K observed by Liu and co-workers [5]. From figure 7 it also emerges that the exchange interaction decreases sharply as the distance between the TM atoms increases. Thus the exchange interaction is short range and could be interpreted as the double exchange mechanism.

4. Summary and conclusions

We have analyzed the electronic structure of GaN doped with TM Mn and Cr with 6.25% and 12.5% doping for various possible geometries to replicate the situation where the TM atoms would appear either to cluster or be separated. The self consistent FP-LAPW calculations predict half metallic state for 6.25% as well as 12.5% doping. Comparing the total energies of the FM and AFM configurations for 12.5% doping, the FM state is found to be lower in energy and is predicted to be the preferred state. On-site magnetic moment at the TM site shows insignificant variation with distance between the dopants. The near neighbor N atoms contribute to the states in energy gap of the semiconductor due to the influence of the TM atoms. Average magnetic moment at nn N site is parallel to the Mn magnetic moment where as it is anti-parallel to the Cr atoms. We observe that both the systems with nn substitution of Mn/Cr atom would show high T_c . The energy gap between the minority spin band in Mn is $\sim 1\text{eV}$ lower than in Cr doped system and we think this could be an important factor in determining a suitable system. But since the magnetic moment at Mn site is higher than Cr, it would be of interest to study mixed systems of Mn and Cr to incorporate the salient features of both TM atoms.

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